

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-100V	16.5mΩ@-10V	-60A



合肥矽普半导体

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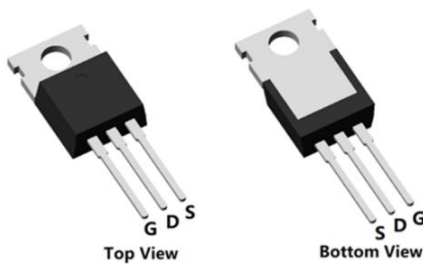
Feature

- Fast Switching
- Low Gate Charge and Rds on
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

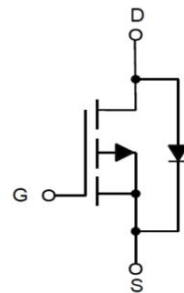
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

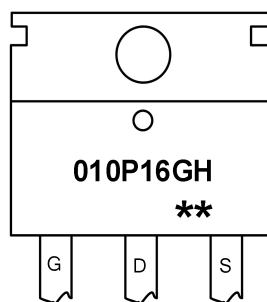


TO-220-3L(1:G 2:D 3:S)

Circuit diagram



Marking



010P16GH : Product code
** : Week code

Order Information

Device	Package	Unit/Tube
SP010P16GHTQ	TO-220-3L	50

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (Tc=25°C)	I_D	-60	A
Continuous Drain Current (Tc=100°C)	I_D	-40	A
Pulsed Drain Current	I_{DM}	-240	A
Single Pulse Avalanche Energy ¹	E_{AS}	625	mJ
Power Dissipation (Tc=25°C)	P_D	180	W
Power Dissipation (Tc=100°C)	P_D	72	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.69	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

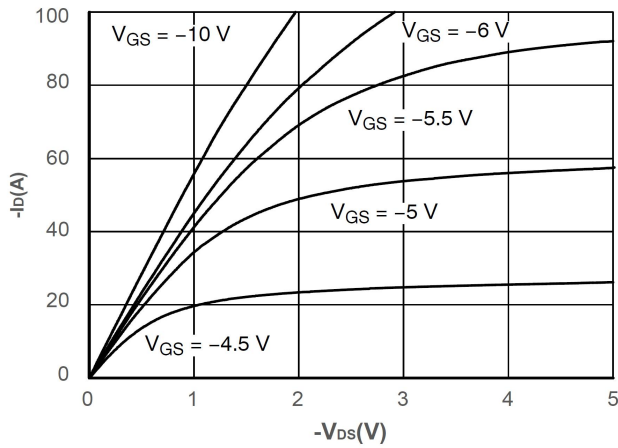
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=-250uA	-100	-	-	V
Drain-Source Leakage Current	IDSS	VDS=-80V , VGS=0V , TJ=25℃	-	-	-1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID=-250uA	-2.6	-3.0	-3.4	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=-10V , ID=-20A	-	16.5	22.5	mΩ
Gate Resistance	RG	VDS=-50V , VGS=0V , f=1MHz	-	3	-	Ω
Dynamic characteristics						
Input Capacitance	Ciss	VDS=-50V , VGS=0V , f=1MHz	-	3786	-	pF
Output Capacitance	Coss		-	681	-	
Reverse Transfer Capacitance	Crss		-	42	-	
Total Gate Charge	Qg	VDS=-50V , VGS=10V , ID=-20A	-	63	-	nC
Gate-Source Charge	Qgs		-	18	-	
Gate-Drain Charge	Qgd		-	10	-	
Gate Plateau Voltage	Vplateau		-	-4.2	-	V
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=-50V , VGS=10V , RG=1.6Ω , ID=-20A	-	9	-	nS
Rise Time	Tr		-	32	-	
Turn-Off Delay Time	Td(off)		-	80	-	
Fall Time	Tf		-	31	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=-1A , TJ=25℃	-	-	-1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	-60	A
Reverse Recovery Time	Trr	IS=-20A , di/dt=100A/us , TJ=25℃	-	96	-	nS
Reverse Recovery Charge	Qrr		-	205	-	nC

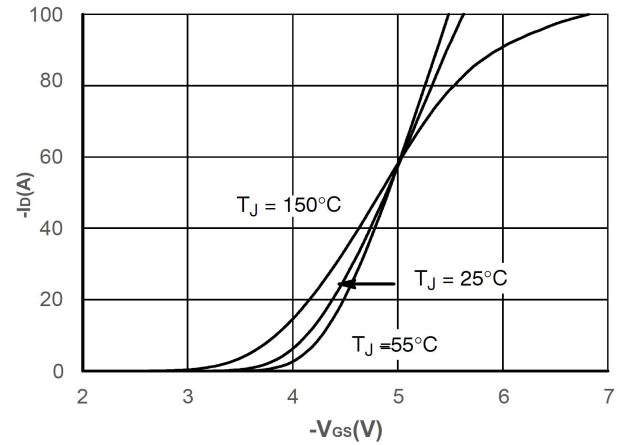
Note :

1. The test condition is $V_{DD}=-50V, V_{GS}=-10V, L=0.5mH, R_G=25\Omega$

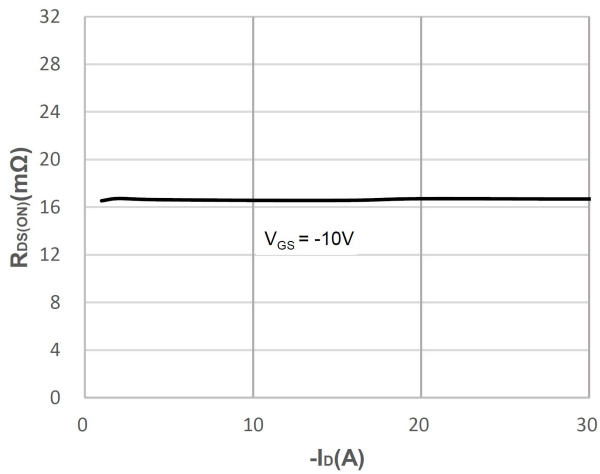
Typical Characteristics



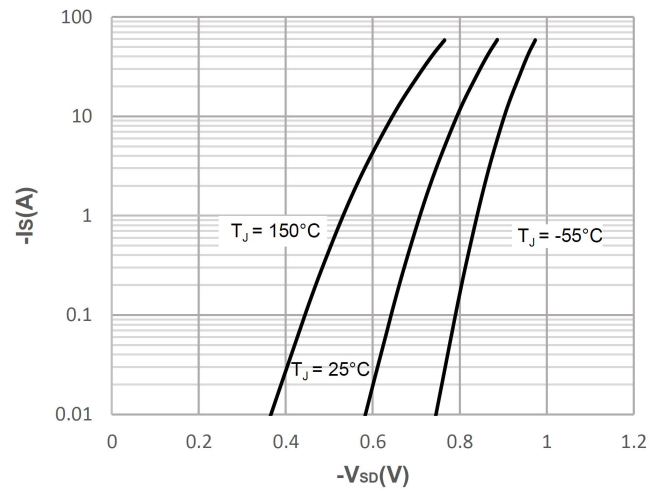
Output Characteristics



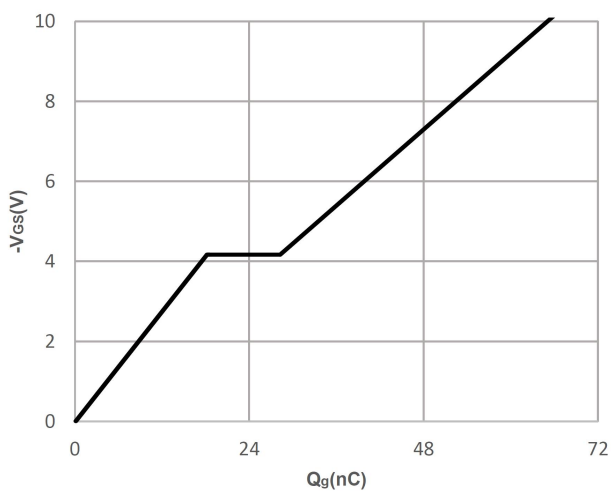
Typical Transfer Characteristics



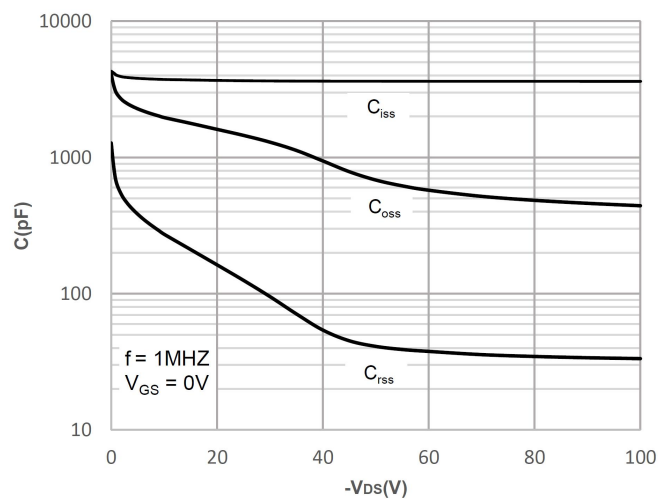
On-resistance vs. Drain Current



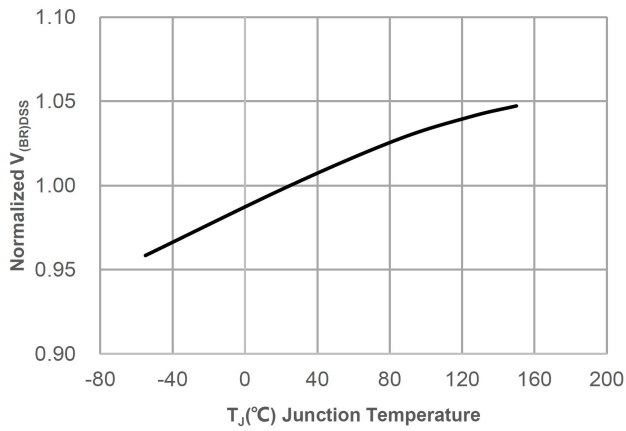
Body Diode Characteristics



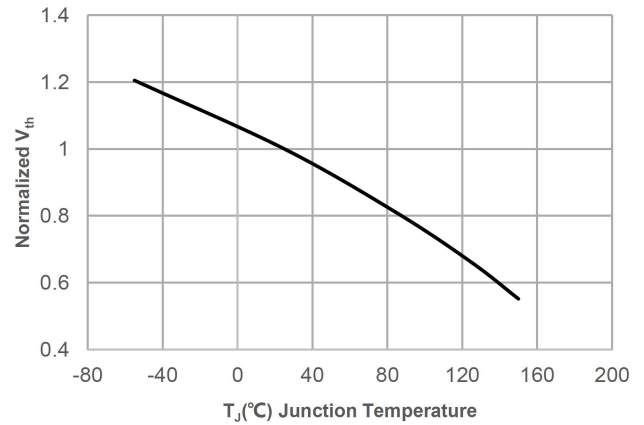
Gate Charge Characteristics



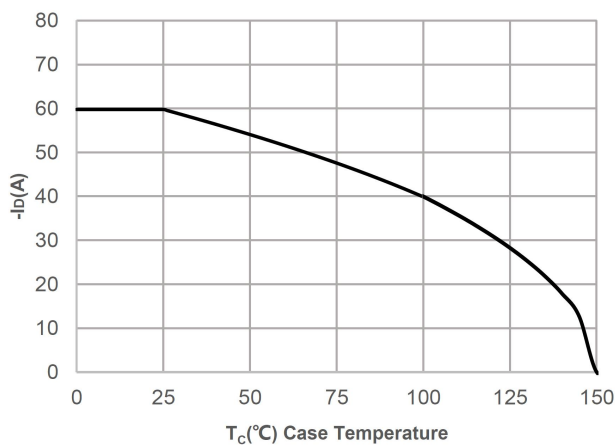
Capacitance Characteristics



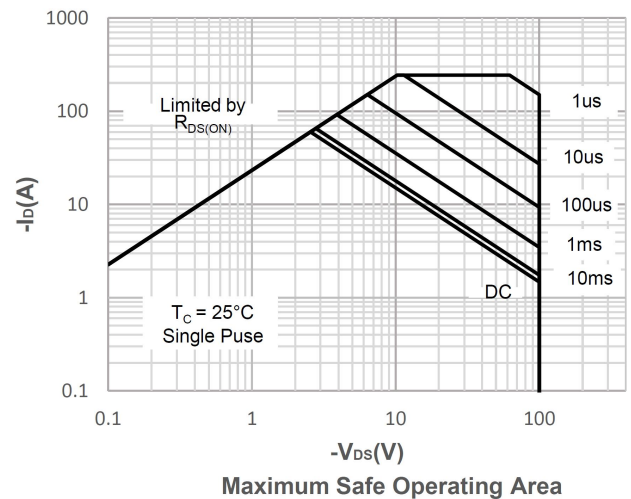
Normalized Breakdown voltage vs. Junction Temperature



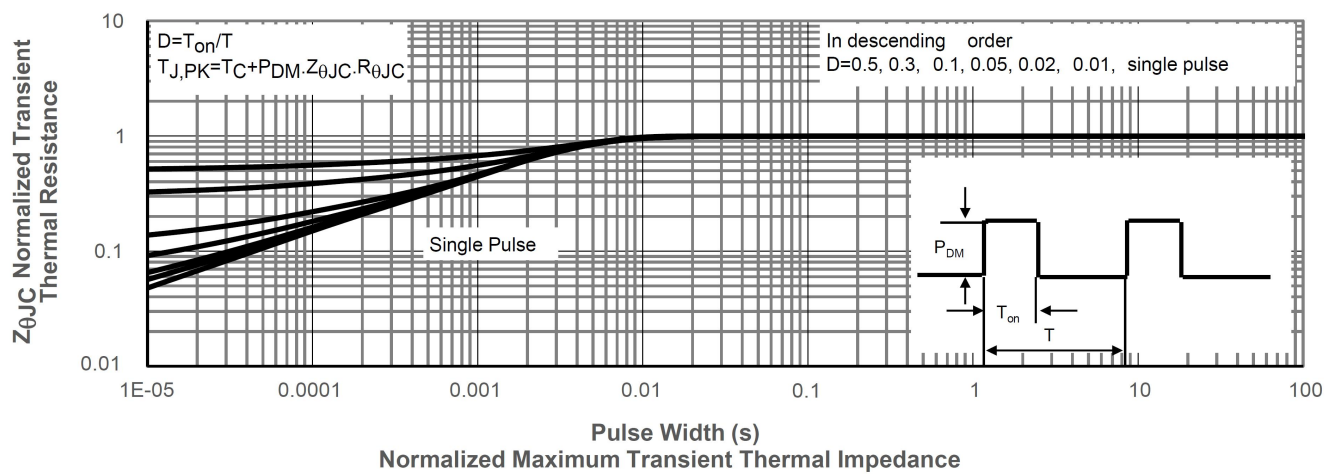
Normalized Threshold Voltage vs. Junction Temperature



Current De-rating

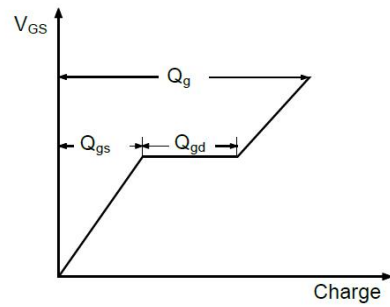
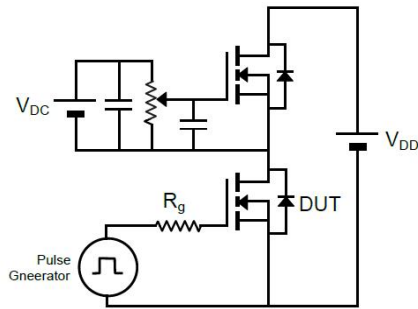


Maximum Safe Operating Area

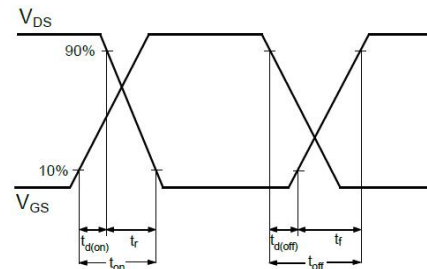
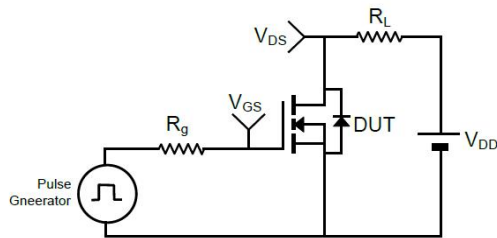


Test Circuit

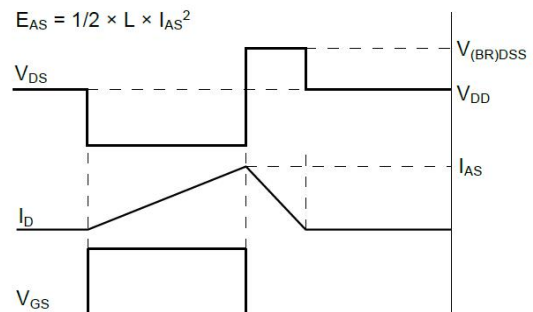
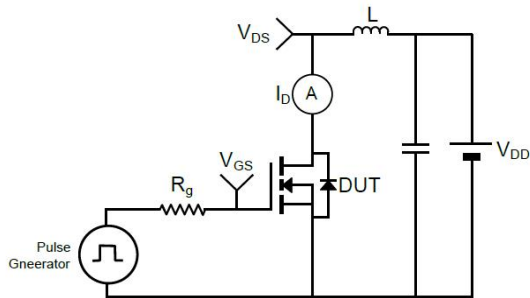
Gate Charge



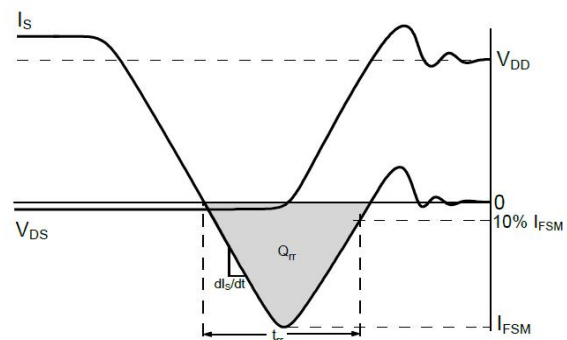
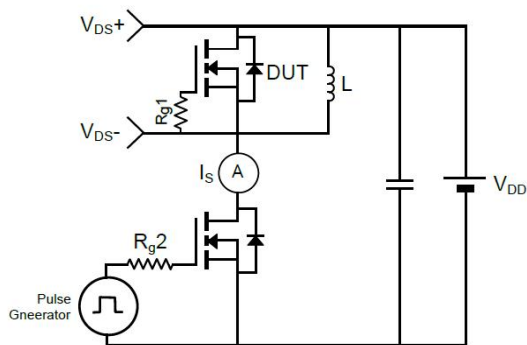
Resistive Load Switching Time



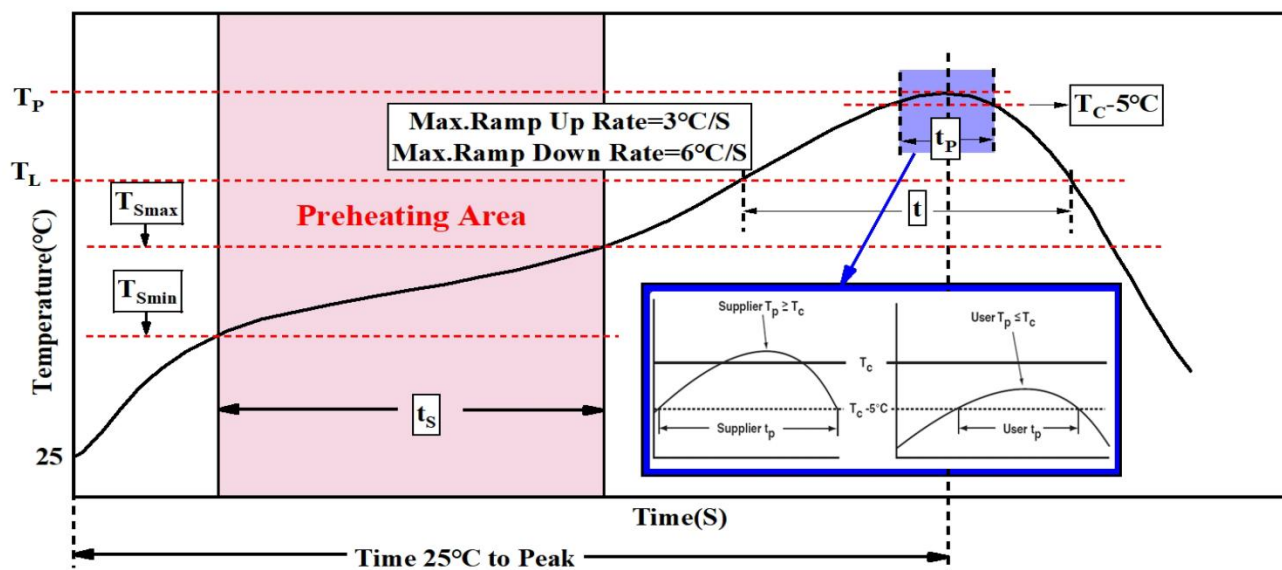
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering(Pb-Free)



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{smin})	100°C	150°C
Temperature max (T _{smax})	150°C	200°C
Time (T _{smin} to T _{smax}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{smax} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

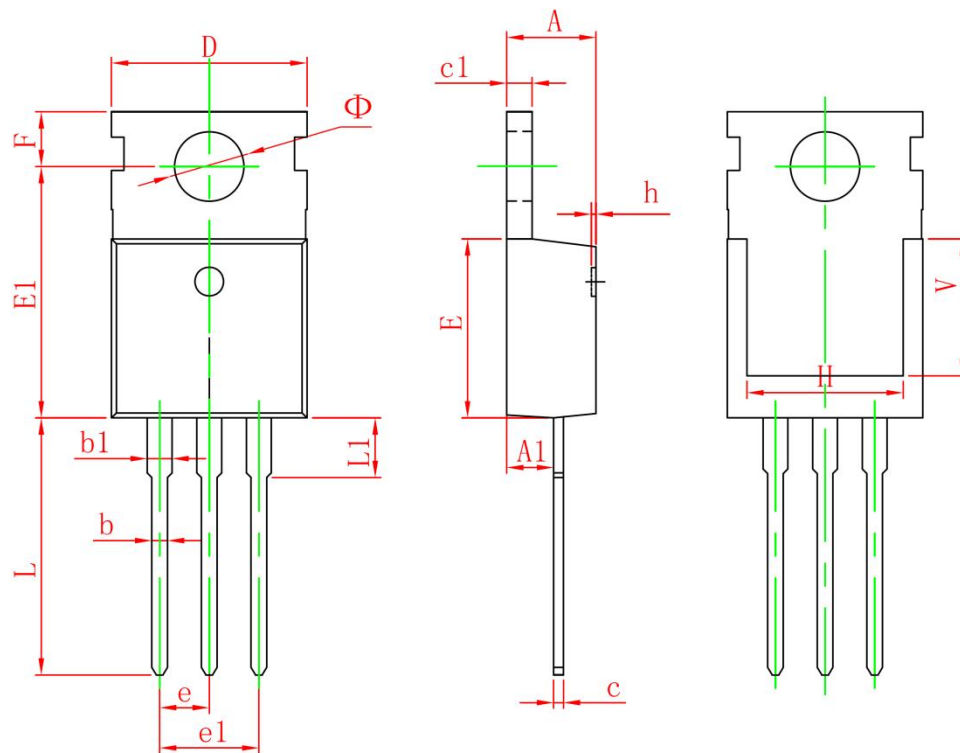
Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-220-3L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.300	4.700
A1	2.200	2.500
b	0.700	0.900
b1	1.100	1.400
c	0.300	0.700
c1	1.200	1.400
D	9.800	10.200
E	9.000	9.400
E1	12.700	13.500
e	2.490	2.590
e1	4.980	5.180
F	2.650	2.950
H	7.600	8.400
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	6.900 REF.	
Φ	3.400	3.800